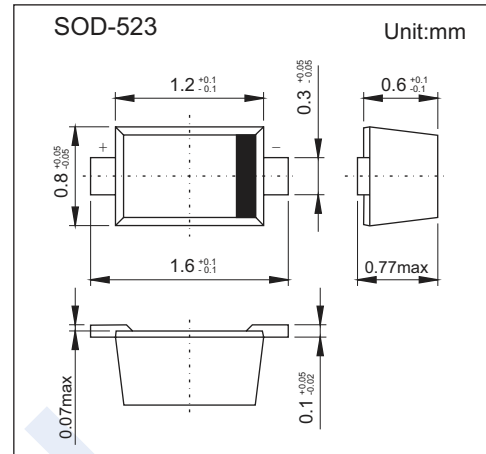


## High Speed Switching Diode

## 1SS387

## ■ Features

- Small package

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	$V_{RM}$	85	V
DC Blocking Voltage	$V_R$	80	
Average Rectified Output Current	$I_o$	100	mA
Peak Forward Surge Current	$I_{FM}$	200	
Surge Current ( $t=10\text{ms}$ )	$I_{surge}$	1000	
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_R$	$I_R = 100 \mu\text{A}$	85			V
Forward voltage	$V_{F1}$	$I_F = 1 \text{ mA}$		0.62		
	$V_{F2}$	$I_F = 10 \text{ mA}$		0.75		
	$V_{F3}$	$I_F = 100 \text{ mA}$			1.2	
Reverse voltage leakage current	$I_{R1}$	$V_R = 30 \text{ V}$			0.1	$\mu\text{A}$
	$I_{R2}$	$V_R = 80 \text{ V}$			0.5	
Capacitance between terminals	$C_T$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			3	pF
Reverse recovery time	$t_{rr}$	$V_R = 6 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$			4	ns

## ■ Marking

Marking	A1
---------	----